



Description

The XPX2060FD uses advanced trench technology and design to provide excellent $R_{DS(ON)}$ with low gate charge. It can be used in a wide variety of applications.

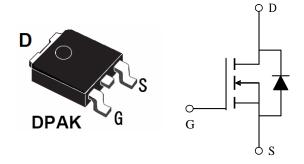
General Features

- High density cell design for ultra low Rdson
- Fully characterized avalanche voltage and current
- Good stability and uniformity with high E_{AS}
- Excellent package for good heat dissipation

Application

- Power switching application
- Hard switched and high frequency circuits
- Uninterruptible power supply

 V_{DS} =20V, I_{D} =85A RDS(ON)=3.7mΩ (typ) @ VGS=4.5V RDS(ON)=5.0mΩ (typ) @ VGS=2.5V



Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
XPX2060FD	XPX2060FD	TO-252-2L	-	-	-

Absolute Maximum Ratings (T_c=25 ℃unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V _{DS}	20	V
Gate-Source Voltage	V _{GS}	±12	V
Drain Current-Continuous	I _D	85	А
Drain Current-Continuous(T _C =100°C)	I _D (100℃)	65	Α
Pulsed Drain Current	I _{DM}	370	А
Maximum Power Dissipation	P _D	85	W
Derating factor		0.58	W/°C
Single pulse avalanche energy (Note 5)	E _{AS}	268	mJ
Operating Junction and Storage Temperature Range	T_J,T_STG	-55 To 175	$^{\circ}$
Thermal Resistance, Junction-to-Case ^(Note 2)	R _{θJC}	1.8	°C/W



Electrical Characteristics (T_C=25°C unless otherwise noted)

Parameter	Symbol	Condition		Тур	Max	Unit
Off Characteristics			•			
Drain-Source Breakdown Voltage	BV _{DSS}	BV _{DSS} V _{GS} =0V I _D =250μA		-	-	V
Zero Gate Voltage Drain Current	I _{DSS}	V_{DS} =20 V , V_{GS} =0 V	-	-	1	μΑ
Gate-Body Leakage Current	I _{GSS}	V _{GS} =±12V,V _{DS} =0V	-	-	±100	nA
On Characteristics (Note 3)						
Gate Threshold Voltage	V _{GS(th)}	$V_{DS}=V_{GS}$, $I_{D}=250\mu A$	0.5	0.75	1.1	V
Drain Course On State Desistance		V _{GS} =4.5V, I _D =20A	_{GS} =4.5V, I _D =20A - 3.7		4.5	mΩ
Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =2.5V, I _D =20A -		5.0	6.5	
Forward Transconductance	g FS	V _{DS} =5V,I _D =20A	20	-	-	S
Dynamic Characteristics (Note4)			•			
Input Capacitance	C _{lss}	V 40VV 0V	-	2016	-	PF
Output Capacitance	Coss	$V_{DS}=10V, V_{GS}=0V,$	-	391	-	PF
Reverse Transfer Capacitance	C _{rss}	F=1.0MHz	-	130	-	PF
Switching Characteristics (Note 4)			•			
Turn-on Delay Time	t _{d(on)}		-	6	-	nS
Turn-on Rise Time	t _r	V_{DD} =10 V , I_D =20 A	-	4	-	nS
Turn-Off Delay Time	t _{d(off)}	V_{GS} =10V, R_{GEN} =2.7 Ω	-	31	-	nS
Turn-Off Fall Time	t _f		-	5	-	nS
Total Gate Charge	Qg	\/ -40\/ L -20A	-	15	-	nC
Gate-Source Charge	Q _{gs}	V_{DS} =10V, I_{D} =20A, V_{GS} =4.5V	-	3	-	nC
Gate-Drain Charge	Q _{gd}	V _{GS} =4.5V	-	4	-	nC
Drain-Source Diode Characteristics						
Diode Forward Voltage (Note 3)	V _{SD}	V _{GS} =0V,I _S =20A	-	-	1.2	V
Diode Forward Current (Note 2)	Is		-	-	90	Α
Reverse Recovery Time	t _{rr}	TJ = 25°C, IF = 20A	-	18	-	nS
Reverse Recovery Charge	Qrr	$di/dt = 100A/\mu s^{(Note3)}$	-	30	-	nC

Notes:

- 1. Repetitive Rating: Pulse width limited by maximum junction temperature.
- **2.** Surface Mounted on FR4 Board, $t \le 10$ sec.
- 3. Pulse Test: Pulse Width ≤ 300µs, Duty Cycle ≤ 2%.
- 4. Guaranteed by design, not subject to production
- **5.** EAS condition: Tj=25 $^{\circ}$ C,V_{DD}=10V,V_G=10V,L=0.5mH,Rg=25 Ω



Typical Electrical and Thermal Characteristics (Curves)

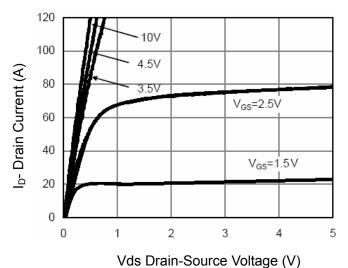


Figure 1 Output Characteristics

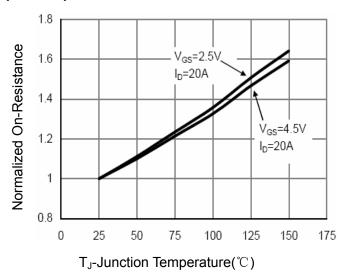
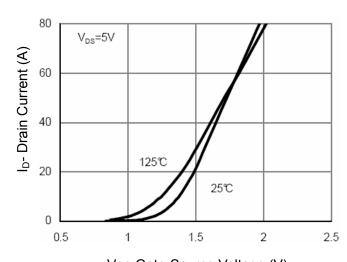


Figure 4 Rdson-Junction Temperature



Vgs Gate-Source Voltage (V)
Figure 2 Transfer Characteristics

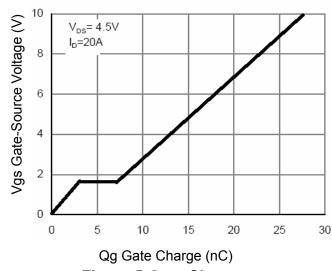


Figure 5 Gate Charge

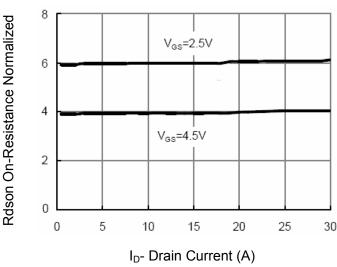


Figure 3 Rdson- Drain Current

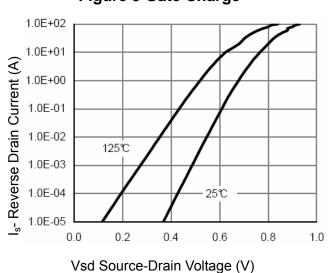


Figure 6 Source- Drain Diode Forward



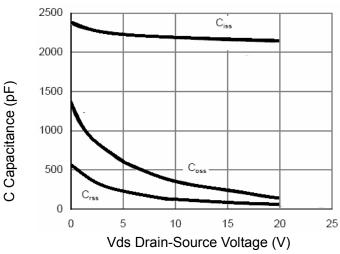


Figure 7 Capacitance vs Vds

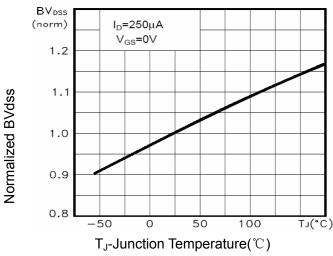


Figure 9 BV_{DSS} vs Junction Temperature

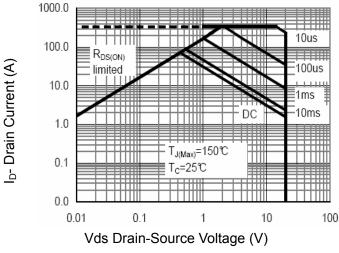


Figure 8 Safe Operation Area

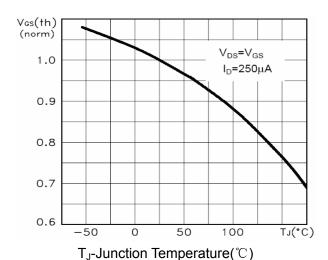


Figure 10 V_{GS(th)} vs Junction Temperature

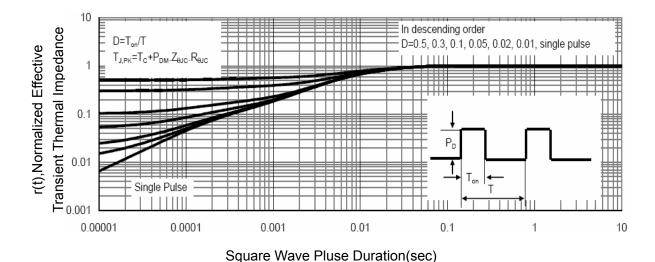
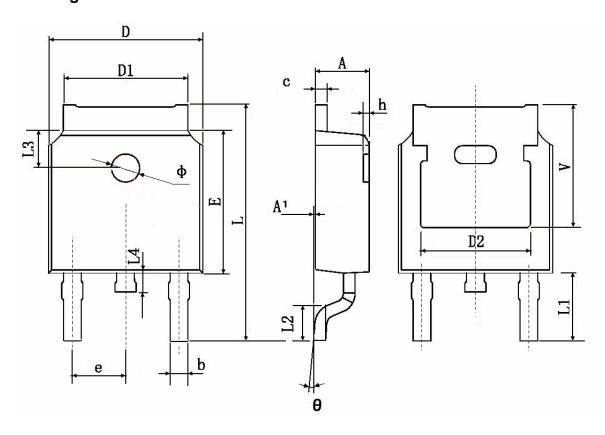


Figure 11 Normalized Maximum Transient Thermal Impedance



TO-252 Package Information



Cumbal	Dimensions	In Millimeters	Dimensions In Inches		
Symbol	Min.	Max.	Min.	Max.	
А	2.200	2.400	0.087	0.094	
A1	0.000	0.127	0.000	0.005	
b	0.660	0.860	0.026	0.034	
С	0.460	0.580	0.018	0.023	
D	6.500	6.700	0.256	0.264	
D1	5.100	5.460	0.201	0.215	
D2	4.830 TYP.		0.190	TYP.	
E	6.000	6.200	0.236	0.244	
е	2.186	2.386	0.086	0.094	
L	9.800	10.400	0.386	0.409	
L1	2.900 TYP.		0.114	TYP.	
L2	1.400	1.700	0.055	0.067	
L3	1.600 TYP.		0.063	3 TYP.	
L4	0.600	1.000	0.024	0.039	
Ф	1.100	1.300	0.043	0.051	
θ	0°	8°	0°	8°	
h	0.000	0.300	0.000	0.012	
V	5.350 TYP.		0.21	1 TYP.	



Flow (wave) soldering (solder dipping)

Product	Peak Temperature	Dipping Time	
Pb device	245℃±5℃ 5sec±1sec		
Pb-Free device	260℃+0/-5℃	5sec±1sec	



This integrated circuit can be damaged by ESD UniverChip Corporation recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedure can cause damage. ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.

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